

Phase out

Thyristor \ Diode Module

PHASE OUT

Phase leg

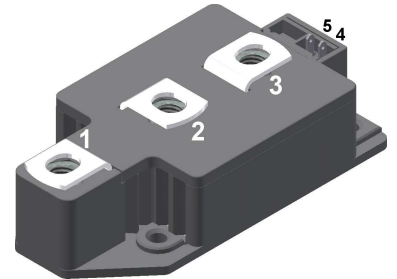
$$V_{RRM} = 2 \times 1400 \text{ V}$$

$$I_{TAV} = 250 \text{ A}$$

$$V_T = 1.14 \text{ V}$$

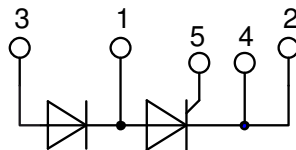
Part number

MCD220-14io1



Backside: isolated

E72873

**Features / Advantages:**

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y2

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Recommended replacement: MCD310-14io1**Terms .Conditions of usage:**

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

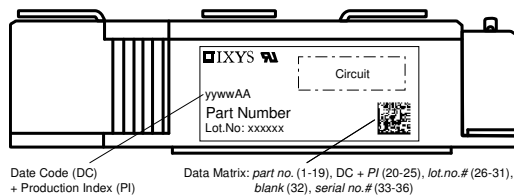
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1500	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1400	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1400\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	mA
		$V_{R/D} = 1400\text{ V}$	$T_{VJ} = 140^{\circ}\text{C}$			40	mA
V_T	forward voltage drop	$I_T = 200\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.24	V
		$I_T = 400\text{ A}$				1.39	V
		$I_T = 200\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.14	V
		$I_T = 400\text{ A}$				1.33	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$			250	A
$I_{T(RMS)}$	RMS forward current	180° sine				400	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}\text{C}$			0.90	V
r_T	slope resistance					1	mΩ
R_{thJC}	thermal resistance junction to case					0.14	K/W
R_{thCH}	thermal resistance case to heatsink				0.040		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			820	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			8.50	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			9.18	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			7.23	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			7.81	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			361.3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			350.6	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			261.0	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			253.4	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		438		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}\text{C}$			120	W
		$t_p = 500\text{ }\mu\text{s}$				60	W
P_{GAV}	average gate power dissipation					20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 750\text{ A}$				100	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 1\text{ A}/\mu\text{s};$ $I_G = 1\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 250\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			1000	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2	V
			$T_{VJ} = -40^{\circ}\text{C}$			3	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
			$T_{VJ} = -40^{\circ}\text{C}$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			0.25	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 1\text{ A}; di_G/dt = 1\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 250\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 50\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$			200		μs

Phase out

Package Y2			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			600	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				255		g
M_D	mounting torque		2.5		5	Nm
M_T	terminal torque		12		15	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0			mm
$d_{Spb/Apb}$		terminal to backside	13.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD220-14io1	MCD220-14io1	Box	2	419281

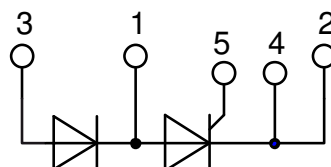
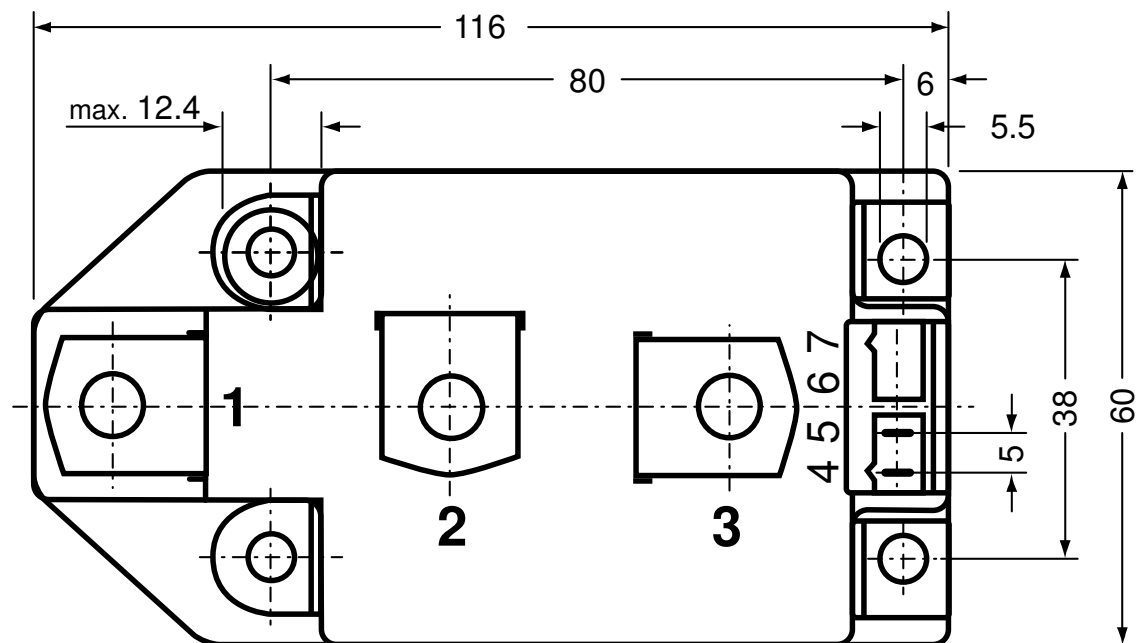
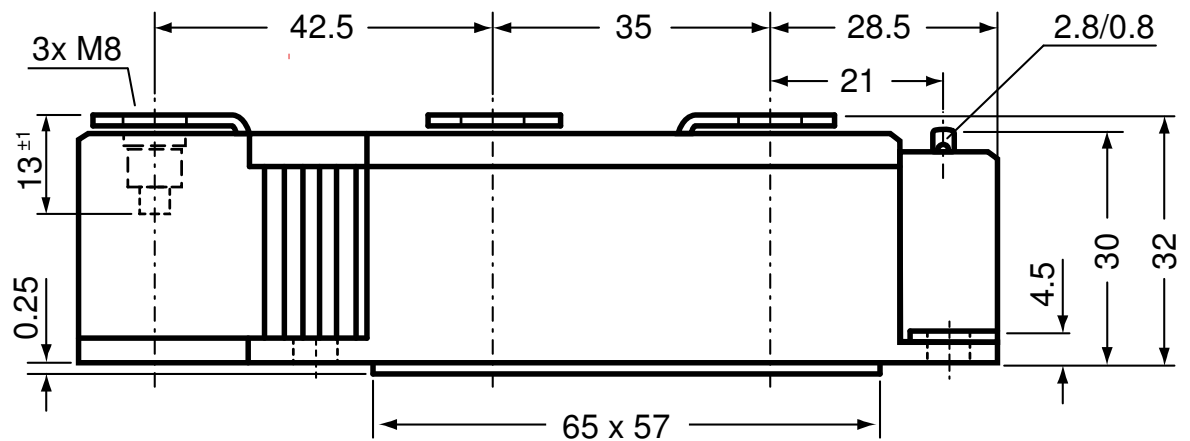
Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 140\text{ °C}$

		Thyristor	
$V_{0\text{ max}}$	threshold voltage	0.9	V
$R_{0\text{ max}}$	slope resistance *	0.5	mΩ

Outlines Y2



Thyristor

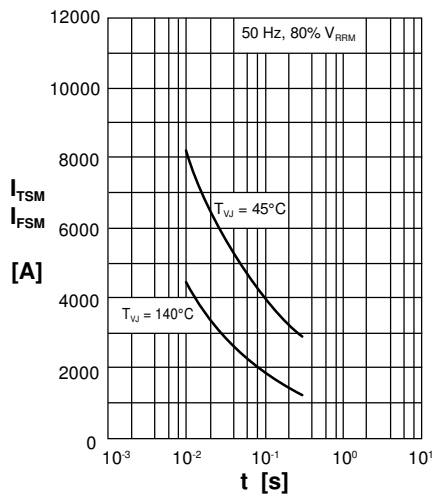


Fig. 1 Surge overload current
 $I_{T(F)SM}$: crest value, t : duration

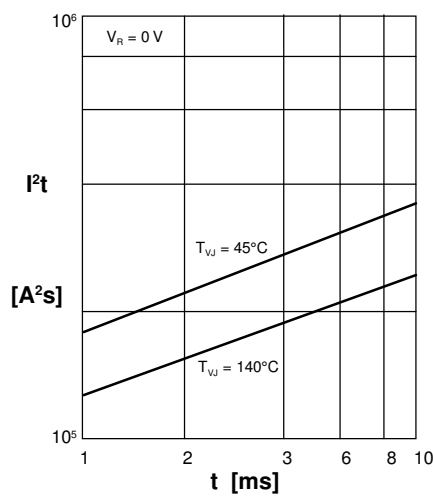


Fig. 2 I^2t versus time (1-10 ms)

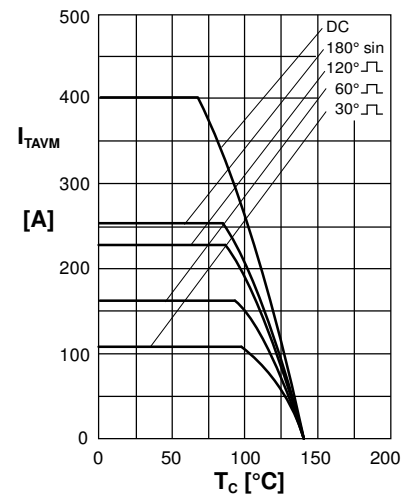


Fig. 3 Max. forward current
at case temperature

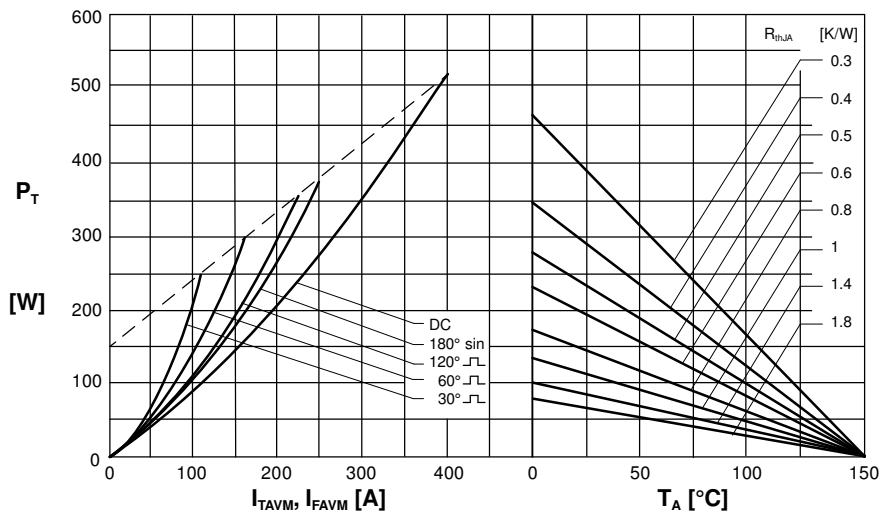


Fig. 4 Power dissipation versus onstate current and
ambient temperature (per thyristor/diode)

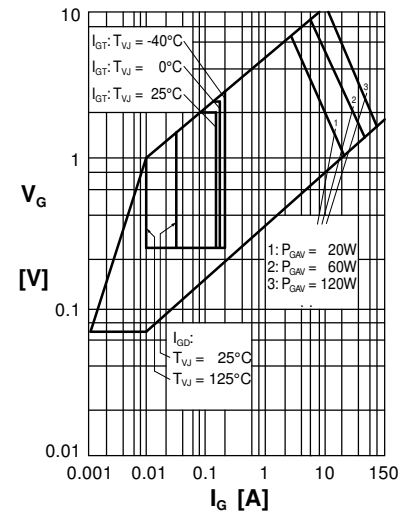


Fig. 5 Gate trigger characteristics

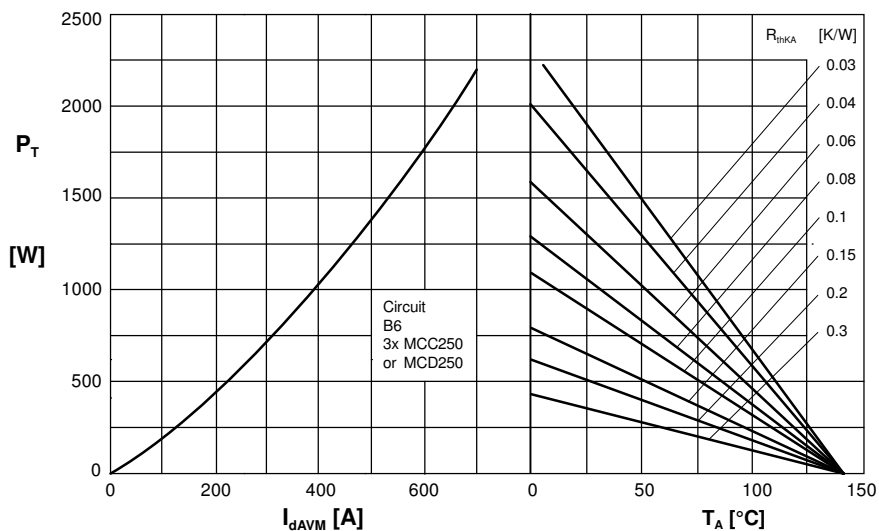


Fig. 6 Three phase rectifier bridge: Power dissipation versus
direct output current and ambient temperature

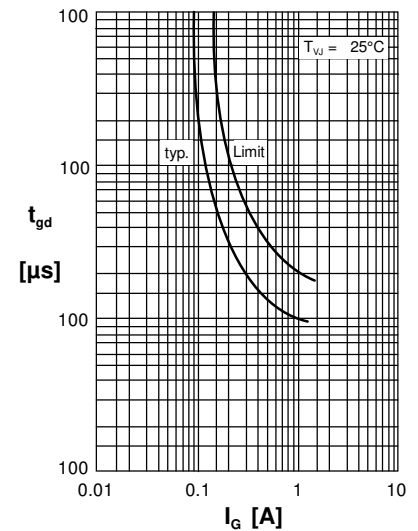


Fig. 7 Gate trigger delay time

Rectifier

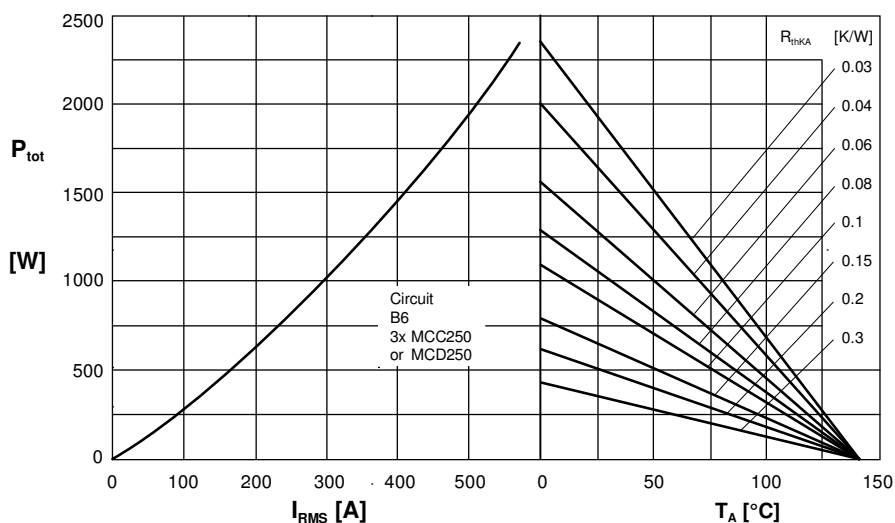


Fig. 7 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

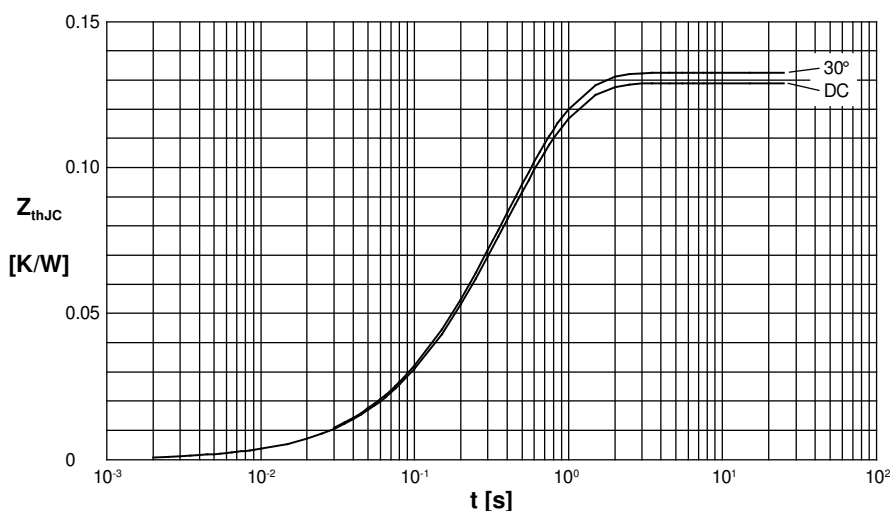


Fig. 8 Transient thermal impedance junction to case (per thyristor/diode)

R_{thJC} for various conduction angles d :

d	R_{thJC} [K/W]
DC	0.139
180°C	0.141
120°C	0.142
60°C	0.142
30°C	0.143

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0037	0.0099
2	0.0177	0.168
3	0.1175	0.456

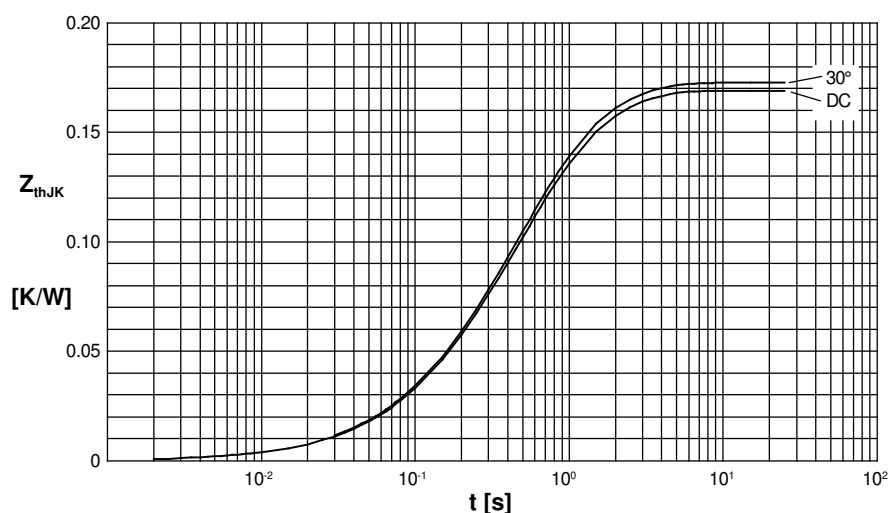


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor/diode)

R_{thJK} for various conduction angles d :

d	R_{thJK} [K/W]
DC	0.179
180°C	0.181
120°C	0.182
60°C	0.183
30°C	0.183

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0033	0.0099
2	0.0159	0.168
3	0.1053	0.456
4	0.04	1.36



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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